

15 V, 0.5 A NPN low VCEsat (BISS) transistor Rev. 1 — 26 January 2012

Product data sheet

1. **Product profile**

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS3515MB.

1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}

1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger

1.4 Quick reference data

- High efficiency due to less heat generation
- AEC-Q101 qualified
- Reduced Printed-Circuit Board (PCB) requirements
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	15	V
I _C	collector current		-	-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	1	А
R _{CEsat}	collector-emitter saturation resistance	I_C = 500 mA; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	360	500	mΩ



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Pinning information 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	E	emitter		3
3	С	collector	2	1
			Transparent top view	2
			SOT883B	sym021

Ordering information 3.

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS2515MB	-	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

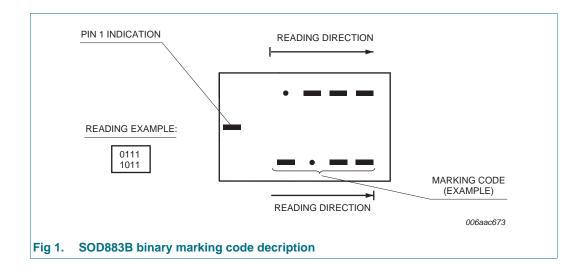
Marking 4.

Table 4.	Marking	codes
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Type number	Marking code ^[1]
PBSS2515MB	0001 0001

[1] For SOT883B binary marking code description, see Figure 1.

4.1 Binary marking code description



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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	15	V
V _{CEO}	collector-emitter voltage	open base		-	15	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1][2]</u>	-	250	mW
			[3][2]	-	590	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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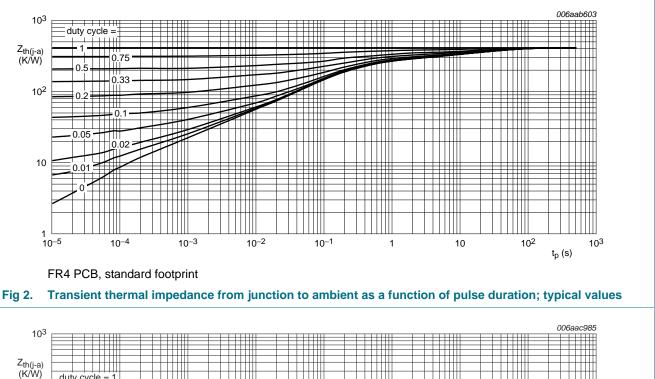
6. Thermal characteristics

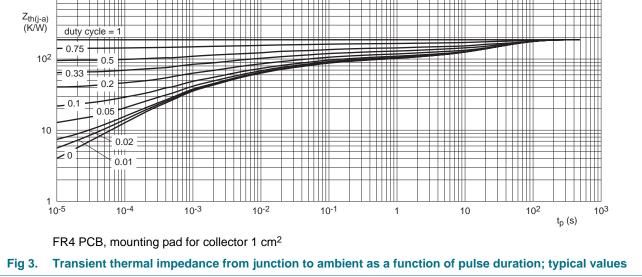
Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1][2]	-	-	500	K/W
	from junction to ambient		[3][2]	-	-	212	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommented soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



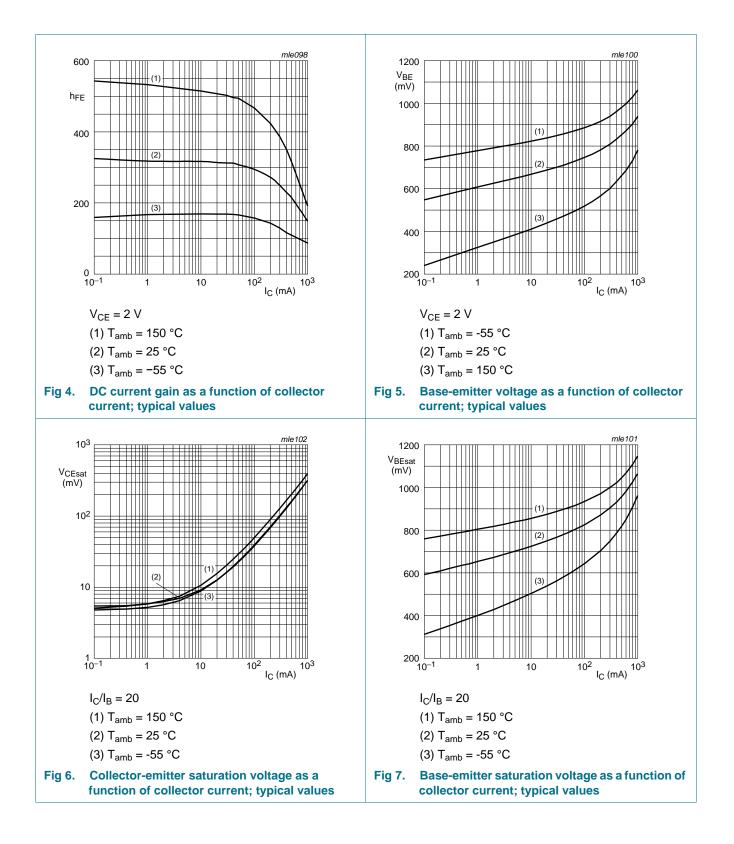


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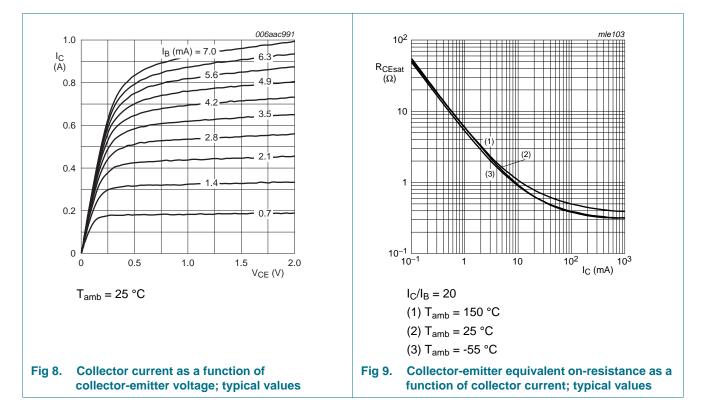
7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = 15 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 15 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 10 mA; T_{amb} = 25 °C	200	-	-	
		$ V_{CE} = 2 \text{ V; } I_C = 100 \text{ mA; pulsed;} $	150	-	-	
		$ V_{CE} = 2 \text{ V; } I_C = 500 \text{ mA; pulsed;} $	90	-	-	
V _{CEsat}	collector-emitter	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C	-	-	25	mV
	saturation voltage	$ I_C = 200 \text{ mA}; I_B = 10 \text{ mA}; \text{pulsed}; $	-	-	150	mV
		I_{C} = 500 mA; I_{B} = 50 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	250	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 500 mA; I_{B} = 50 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	360	500	mΩ
V _{BEsat}	base-emitter saturation voltage	$ I_C = 500 \text{ mA}; I_B = 50 \text{ mA}; \text{pulsed}; t_p \le 300 \mu\text{s}; \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C} $	-	-	1.1	V
V _{BEon}	base-emitter turn-on voltage	$ V_{CE} = 2 \text{ V; } I_C = 100 \text{ mA; pulsed;} $	-	-	0.9	V
f _T	transition frequency	V_{CE} = 5 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	250	420	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	4.4	6	pF

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8. Test information

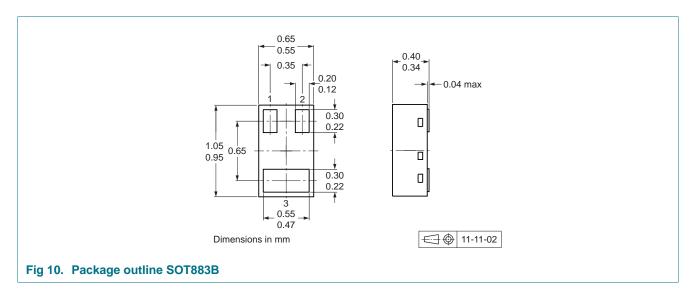
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors and is suitable for use in automotive applications.

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9. Package outline



10. Soldering

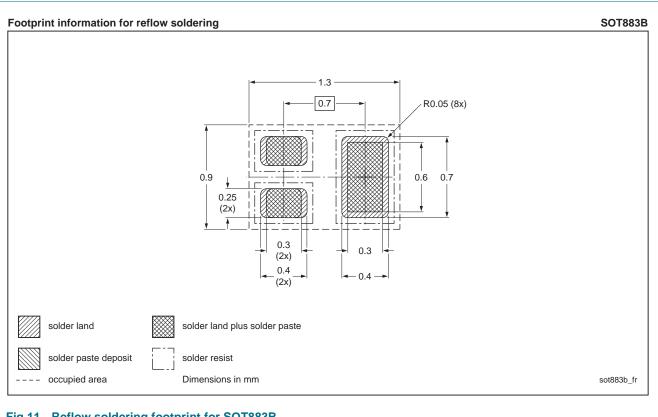


Fig 11. Reflow soldering footprint for SOT883B

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11. Revision history

Table 8. Revi	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS2515MB v.	1 20120126	Product data sheet	-	-			

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12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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